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N-Channel 40 V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | | |
|---------------------|----------------------------------|---------------------------------|-----------------------|--|--|--|
| V _{DS} (V) | $R_{DS(on)}$ (m Ω)(Typ.) | I _D (A) ^a | Q _g (Typ.) | | | |
| 40 | 2.2 at V _{GS} = 10 V | 100 | 120 nC | | | |
| 40 | 3.8 at V _{GS} = 10 V | 100 | | | | |

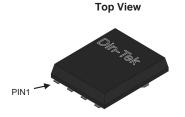
FEATURES

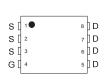
- DT-Trench Power MOSFET
- 100 % R_q and UIS Tested
- 100% Avalanche Test

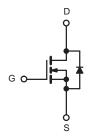
APPLICATIONS

- · Load switching
- · Hard switched and high frequency circuits
- · Uninterruptible power supply

DFN5X6-8L Pin Configuration







N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted) | | | | | |
|---|-------------------------|-----------------------------------|---------------|----|--|
| PARAMETER | SYMBOL | LIMIT | UNIT | | |
| Drain-Source Voltage | V _{DS} | 40 | V | | |
| Gate-Source Voltage | V _{GS} | ± 20 | V | | |
| Continuous Drain Current (T _J = 150 °C) ^a | T _C = 25 °C | I _D | 100 | А | |
| Continuous Diam Current (1) = 150 °C) ³ | T _C = 100 °C | l _D | 83 | | |
| Pulsed Drain Current ^b | I _{DM} | 360 | | | |
| Single Avalanche Energy | E _{AS} | 208 | mJ | | |
| Maximum Power Dissipation ^c | T _C = 25 °C | P _D | 96 | W | |
| wiaximum rower bissipation | T _C = 100 °C | T FD | 36.8 | VV | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to + 150 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|-------------------|-------|------|--|--|
| PARAMETER | SYMBOL | LIMIT | UNIT | | |
| Junction-to-Ambient (PCB Mount) ^d | R_{thJA} | 50 | °C/W | | |
| Junction-to-Case (Drain) | R _{thJC} | 1.3 | C/VV | | |

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. $\,$ Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{8JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



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| SPECIFICATIONS (T _C = 25 °C, unless otherwise noted) | | | | | | | |
|---|---------------------|---|------|------|-------|-------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
| Static | | | T | 1 | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | 40 | - | - | V | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | 1 - | | 2 | · | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | - | - | ± 100 | nA | |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = 40 V, V_{GS} = 0 V$ | - | - | 1 | μA | |
| Zero Gate Voltage Brain Guirent | | $V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$ | - | - | 100 | | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 100 | - | - | Α | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | $V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$ | - | 2.2 | 3.2 | mΩ | |
| Brain Godice on State Resistance | 1 (DS(on) | $V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$ | - | 3.8 | 5 | 11177 | |
| Forward Transconductance ^a | 9 _{fs} | $V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$ | - | 43 | - | S | |
| Dynamic ^b | | | | | | | |
| Input Capacitance | C _{iss} | | - | 6500 | - | pF | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$ | - | 473 | - | | |
| Reverse Transfer Capacitance | C _{rss} | | - | 447 | - | | |
| Total Gate Charge ^c | Qg | | - | 120 | - | nC | |
| Gate-Source Charge ^c | Q _{gs} | $V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$ | - | 13.2 | - | | |
| Gate-Drain Charge ^c | Q_{gd} | | - | 20.2 | - | | |
| Gate Resistance | Rg | f = 1 MHz | - | 1.1 | - | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | | - | 15 | - | | |
| Rise Time ^c | t _r | $V_{DS} = 20 \text{ V}, I_D = 10 \text{ A},$ | - | 17 | - | | |
| Turn-Off Delay Time ^c | t _{d(off)} | $R_g = 3\Omega$, $V_{GS} = 10 V$ | - | 52 | - | ns | |
| Fall Time ^c | t _f | | - | 23 | - | | |
| Drain-Source Body Diode Ratings and | Characterist | ics b (T _C = 25 °C) | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | - | - | 100 | Α | |
| Pulsed Current | I _{SM} | | - | - | 360 | Α | |
| Forward Voltage ^a | V_{SD} | I _F = 30 A, V _{GS} = 0 V | - | - | 1.2 | V | |
| Reverse Recovery Time | t _{rr} | 1 20 4 4:/4: 422 4/ | - | 42 | - | ns | |
| Reverse Recovery Charge | Q _{rr} | I _F = 30 A, di/dt = 100 A/μs | - | 45 | - | nC | |

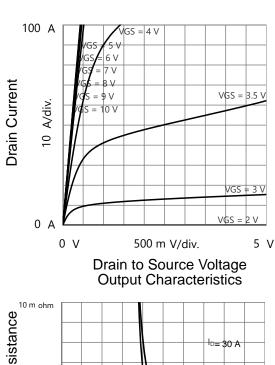
Notes

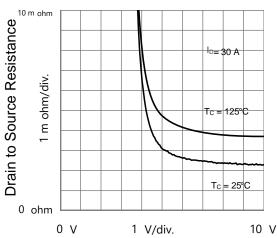
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

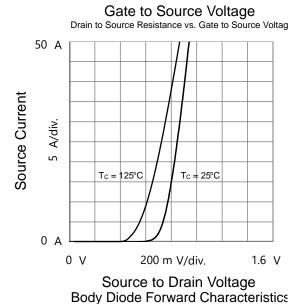
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

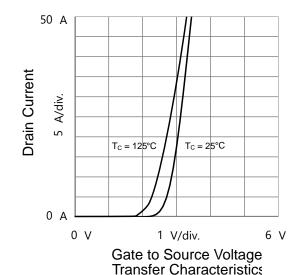


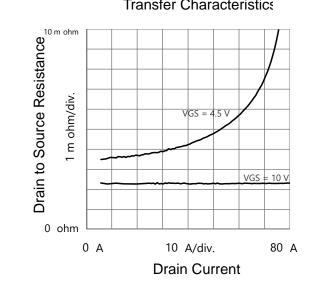
TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

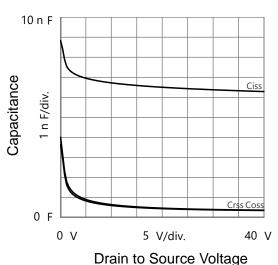








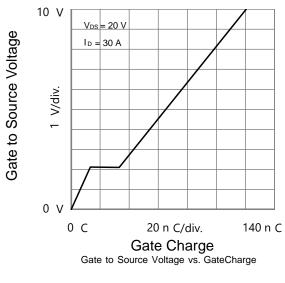


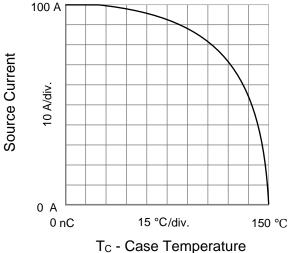


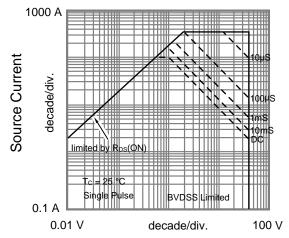
Capacitances



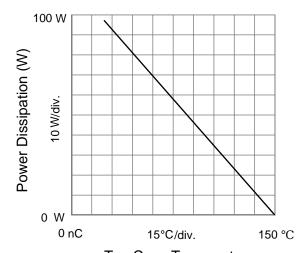
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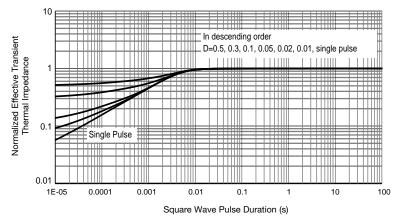




Source to Drain Voltage Safe Operating Area, Junction-to-Case



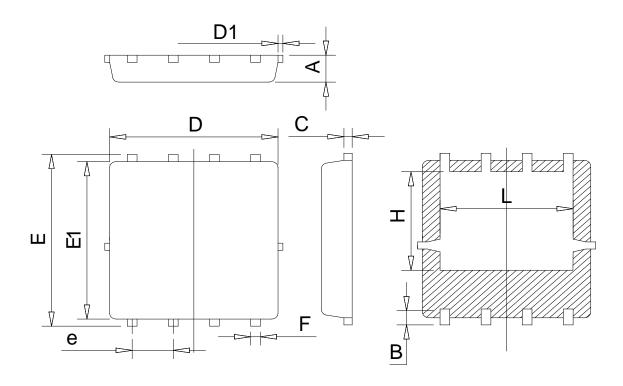
T_C - Case Temperature



Normalized Thermal Transient Impedance, Junction-to-Case



PDFN5X6 PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

| Symbol | Min | Тур | Max |
|--------|------|-------|------|
| Α | 0.78 | 0.95 | 1.12 |
| В | 0.45 | 0.58 | 0.78 |
| С | 0.18 | 0.254 | 0.36 |
| D | 4.70 | 5.20 | 5.45 |
| D1 | | | 0.18 |
| Е | 5.85 | 6.05 | 6.25 |
| E1 | 5.38 | 5.55 | 5.98 |
| е | 1.15 | 1.27 | 1.40 |
| F | 0.18 | 0.30 | 0.52 |
| Н | 3.25 | 3.47 | 3.70 |
| L | 3.75 | 4.00 | 4.25 |





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